

# RBN25H125S1FPQ-A0

1250V - 25A - IGBT

Application: Uninterruptible Power Supply

R07DS1378EJ0004

Rev.0.04

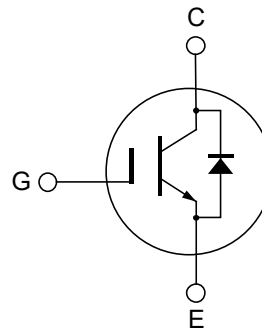
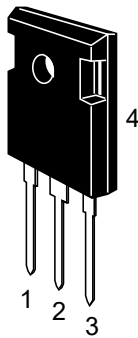
Dec 28, 2016

## Features

- Low collector to emitter saturation voltage  
 $V_{CE(sat)} = 1.8 \text{ V typ. (at } I_C = 25 \text{ A, } V_{GE} = 15 \text{ V, } T_a = 25^\circ\text{C)}$
- Built in fast recovery diode in one package
- Trench gate and thin wafer technology (G8H series)
- High speed switching
- Short circuit withstands time (10  $\mu\text{s min.}$ )

## Outline

RENESAS Package code: PRSS0003ZH-A  
 (Package name: TO-247A)



1. Gate
2. Collector
3. Emitter
4. Collector

## Absolute Maximum Ratings

( $T_c = 25^\circ\text{C}$ )

Item	Symbol	Ratings	Unit
Collector to emitter voltage	$V_{CES} / V_R$	1250	V
Gate to emitter voltage	$V_{GES}$	$\pm 30$	V
Collector current	$T_c = 25^\circ\text{C}$	$I_C$	50
	$T_c = 100^\circ\text{C}$	$I_C$	25
Collector peak current	$I_{C(\text{peak})}$ <sup>Note1</sup>	(75)	A
Collector to emitter diode Forward current	$T_c = 25^\circ\text{C}$	$I_{DF}$	30
	$T_c = 100^\circ\text{C}$	$I_{DF}$	15
Collector to emitter diode forward peak current	$I_{DF(\text{peak})}$ <sup>Note1</sup>	(75)	A
Collector dissipation	$P_C$ <sup>Note 2</sup>	(272)	W
Junction to case thermal impedance (IGBT)	$\theta_{j-c}$	(0.55)	$^\circ\text{C/W}$
Junction to case thermal resistance (Diode)	$\theta_{j-cd}$	(1.83)	$^\circ\text{C/W}$
Junction temperature	$T_j$ <sup>Note2</sup>	175	$^\circ\text{C}$
Storage temperature	$T_{stg}$	-55 to +150	$^\circ\text{C}$

Note: Continuous heavy condition (e.g. high temperature/voltage/current or high variation of temperature) may affect a reliability even if it are within the absolute maximum ratings. Please consider derating condition for appropriate reliability in reference Renesas Semiconductor Reliability Handbook (Recommendation for Handling and Usage of Semiconductor Devices) and individual reliability data.

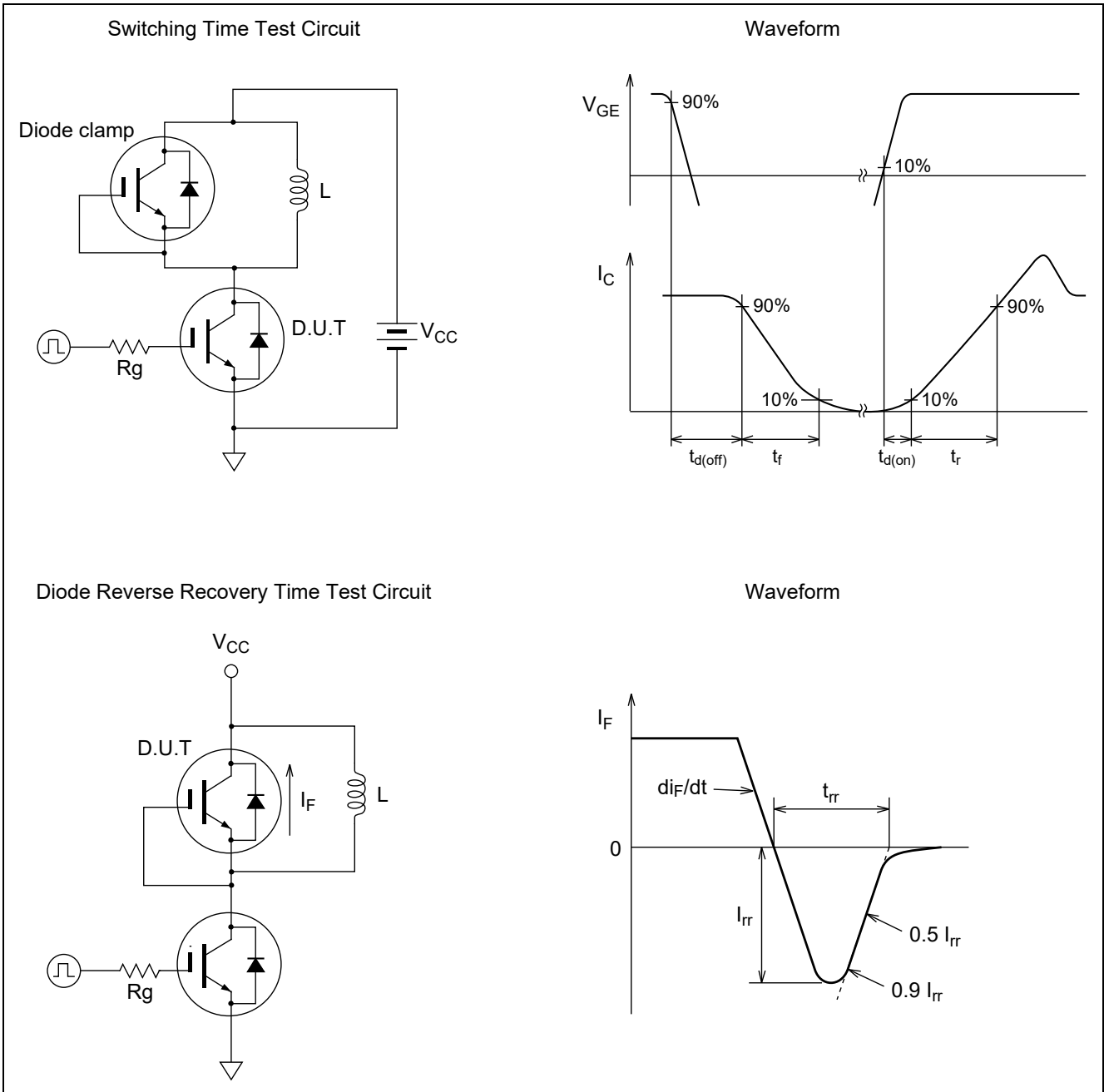
## Electrical Characteristics

(Ta = 25°C)

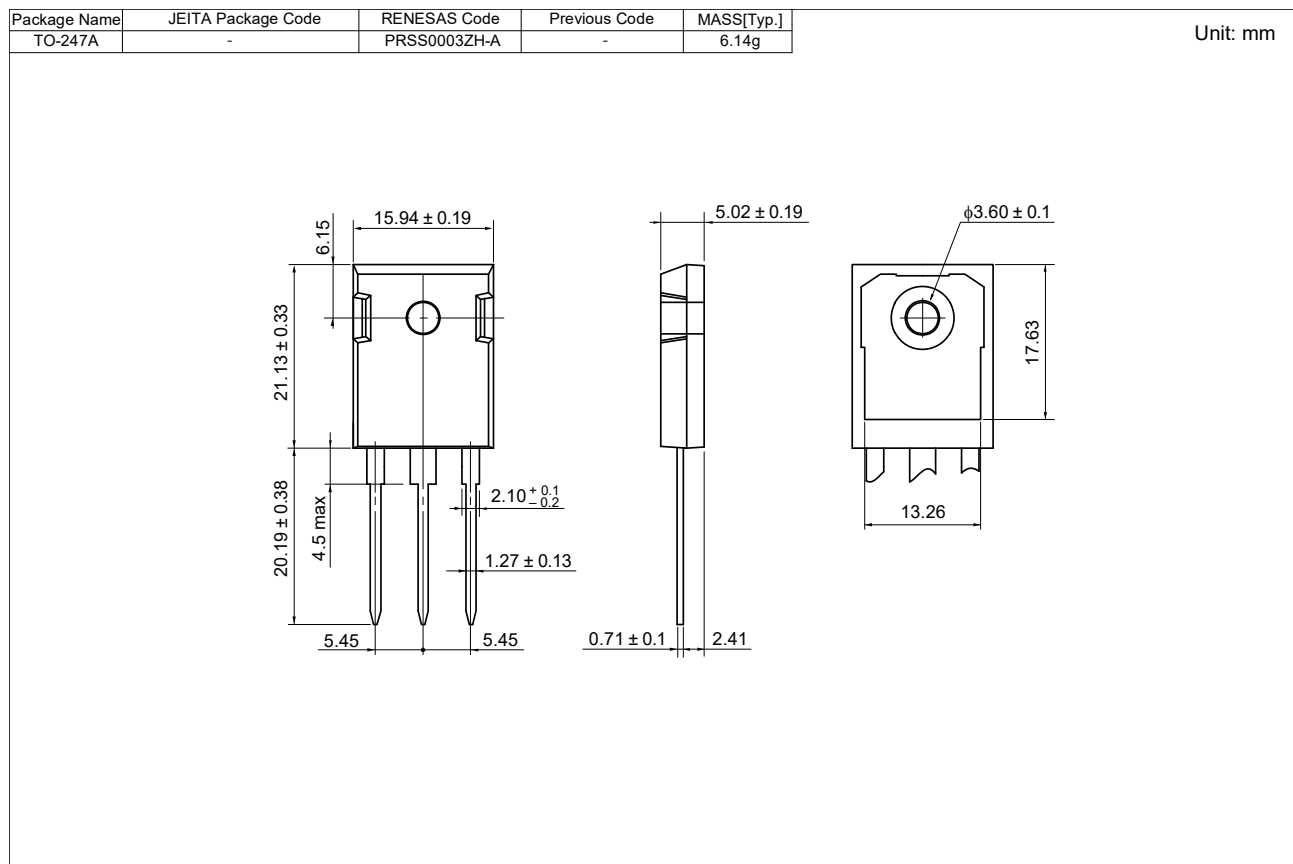
Item	Symbol	Min	Typ	Max	Unit	Test Conditions
Zero gate voltage collector current / Diode reverse current	$I_{CES} / I_R$	—	—	(200)	$\mu\text{A}$	$V_{CE} = 1250 \text{ V}, V_{GE} = 0$
Gate to emitter leak current	$I_{GES}$	—	—	( $\pm 1$ )	$\mu\text{A}$	$V_{GE} = \pm 30 \text{ V}, V_{CE} = 0$
Gate to emitter cutoff voltage	$V_{GE(off)}$	(5.0)	—	(6.8)	V	$V_{CE} = 10 \text{ V}, I_C = 0.83 \text{ mA}$
Collector to emitter saturation voltage	$V_{CE(sat)}$	—	(1.8)	(2.34)	V	$I_C = 25 \text{ A}, V_{GE} = 15 \text{ V}$ <sup>Note3</sup>
Input capacitance	$C_{ies}$	—	(1770)	—	pF	$V_{CE} = 25 \text{ V}$ $V_{GE} = 0$ $f = 1 \text{ MHz}$
Output capacitance	$C_{oes}$	—	(87)	—	pF	
Reverse transfer capacitance	$C_{res}$	—	(12)	—	pF	
Total gate charge	$Q_g$	—	(65)	—	nC	$V_{GE} = 15 \text{ V}$ $V_{CE} = 600 \text{ V}$ $I_C = 25 \text{ A}$
Gate to emitter charge	$Q_{ge}$	—	(19)	—	nC	
Gate to collector charge	$Q_{gc}$	—	(34)	—	nC	
Turn-on delay time	$t_{d(on)}$	—	(20)	—	ns	$V_{CC} = 600 \text{ V}$ $V_{GE} = 15 \text{ V}$ $I_C = 25 \text{ A}$ $R_g = 10 \Omega$ $T_c = 25^\circ\text{C}$ Inductive load <sup>Note4</sup>
Rise time	$t_r$	—	(8.3)	—	ns	
Turn-off delay time	$t_{d(off)}$	—	(103)	—	ns	
Fall time	$t_f$	—	(211)	—	ns	
Turn-on loss energy	$E_{on}$	—	(0.76)	—	mJ	
Turn-off loss energy	$E_{off}$	—	(0.78)	—	mJ	
Total switching energy	$E_{total}$	—	(1.54)	—	mJ	
Turn-on delay time	$t_{d(on)}$	—	(18)	—	ns	
Rise time	$t_r$	—	(11)	—	ns	
Turn-off delay time	$t_{d(off)}$	—	(115)	—	ns	
Fall time	$t_f$	—	(243)	—	ns	
Turn-on loss energy	$E_{on}$	—	(1.18)	—	mJ	$V_{CC} = 600 \text{ V}$ $V_{GE} = 15 \text{ V}$ $I_C = 25 \text{ A}$ $R_g = 10 \Omega$ $T_c = 150^\circ\text{C}$ Inductive load <sup>Note4</sup>
Turn-off loss energy	$E_{off}$	—	(1.58)	—	mJ	
Total switching energy	$E_{total}$	—	(2.76)	—	mJ	
Short circuit withstand time <sup>Note5</sup>	$t_{sc}$	(10)	—	—	$\mu\text{s}$	
Short circuit collector saturation current <sup>Note5</sup>	$I_{c,sc}$	(75)	—	—	A	$V_{CC} \leq 720 \text{ V}, V_{GE} = 15 \text{ V}$ $T_c \leq 150^\circ\text{C}$
FRD forward voltage	$V_F$	—	(2.9)	(3.77)	V	$I_F = 15 \text{ A}$ <sup>Note3</sup>
FRD reverse recovery time	$t_{rr}$	—	(100)	—	ns	$I_F = 15 \text{ A}, di_F/dt = 300 \text{ A}/\mu\text{s}$
FRD reverse recovery charge	$Q_{rr}$	—	(0.52)	—	$\mu\text{C}$	
FRD peak reverse recovery current	$I_{rr}$	—	(9)	—	A	

## Notes:

1.  $PW \leq 10 \mu\text{s}$ , duty cycle  $\leq 1\%$
2. Please use this device in the thermal conditions which the junction temperature does not exceed  $175^\circ\text{C}$ .  
Renesas IGBT Application Note is disclosed about reliability test and application condition up to  $175^\circ\text{C}$ .
3. Pulse test
4. Switching time test circuit and waveform are shown below.
5. Verified by design.



## Package Dimensions



## Ordering Information

Orderable Part Number	Quantity	Shipping Container
RBN25H125S1FPQ-A0#CB0	240 pcs	Box (Tube)

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